

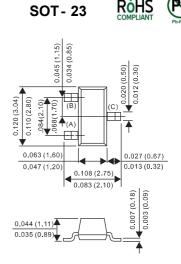
PNP Silicon General Purpose Transistors

Features

- High current capacity in compact package Ic = -1.5A
- Epitaxial planar type
- Pb-free package is available
- Suffix "-H" indicates Halogen-free part

Mechanical Data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.008 gram



Dimensions in inches and (millimeters)

Maximum ratings (AT T_A=25°C unless otherwise noted)

PARAMETER	Symbol	Value	UNIT
Collector-base voltage	V _{CBO}	-40	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{ebo}	-5.0	V
Collector current-continuoun	l _c	- 1500	mAdc

Thermal characteristics

PARAMETER		Symbol	MIN.	TYP.	MAX.	UNIT
Total device dissipation FR-5 board	$T_A = 25^{\circ}C$	P _D			225	mW
(1)	Derate above 25° C				1.8	mW/°C
Thermal resistance	Junction to ambient	$R_{_{\theta JA}}$			556	°C/W
Total device dissipation alumina	$T_A = 25^{\circ}C$	P _D			300	mW
substrate(2)	Derate above 25° C				2.4	mW/°C
Thermal resistance	Junction to ambient	$R_{_{\theta JA}}$			417	°C/W
Operating junction temperature range		T	-55		+150	°C
Storage temperature range			-55		+150	°C

1.FR-5 = 1.0 X 0.75 X0.062 in.

2.Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.



Electrical characteristics (AT T_A=25°C unless otherwise noted)

Off characteristics

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Collector-base breakdown voltage	I _c = -100uA	V _{(BR)CBO}	-40			V
Collector-emitter breakdown voltage	I _c = -1.0mA	V _{(BR)CEO}	-25			V
Emitter-base breakdown voltage	I _E = -100uA	V _{(BR)EBO}	-5.0			V
Collector cutoff current	V _{CB} = -35V	I _{сво}			-150	nA
Emitter cutoff current	$V_{EB} = -4.0V$	I _{EBO}			-150	nA

On characteristics

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
DC current gain	I _c = -100mA, V _{CE} = -1.0V	h _{FE} *Note	100		600	
Collector-emitter saturation voltage	I _c = -800mA, I _B = -80mA	V _{CE(sat)}			-0.5	V

Note	*	L	Н	J		
Note	hfe	120~200	200~350	300~400		



Rating and characteristic curves

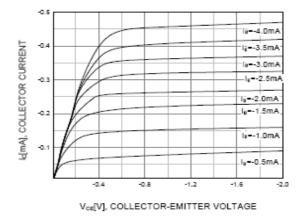


Figure 1. Static Characteristic

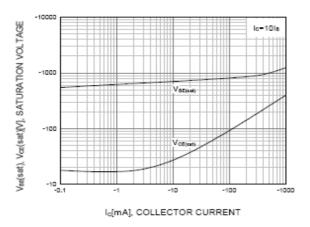


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

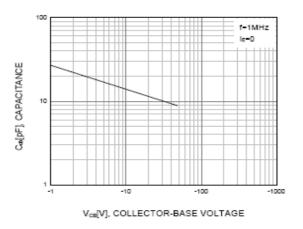
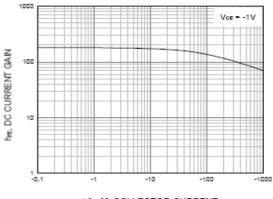


Figure 5. Collector Output Capacitance



Id[mA], COLLECTOR CURRENT

Figure 2. DC current Gain

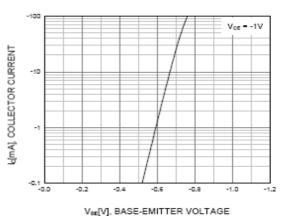


Figure 4. Base-Emitter On Voltage

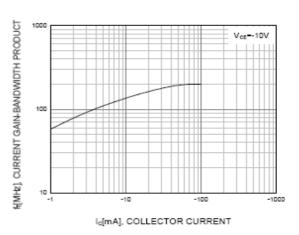
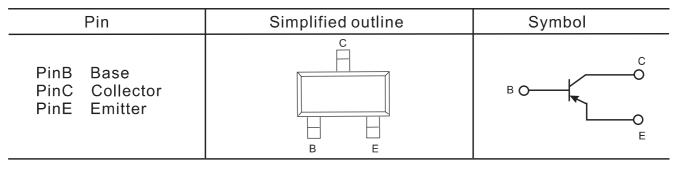


Figure 6. Current Gain Bandwidth Product



Pinning information

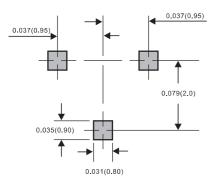


Marking

Type number	Marking code		
MMBTSS8550	Y2		

Suggested solder pad layout





Dimensions in inches and (millimeters)

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